



Description

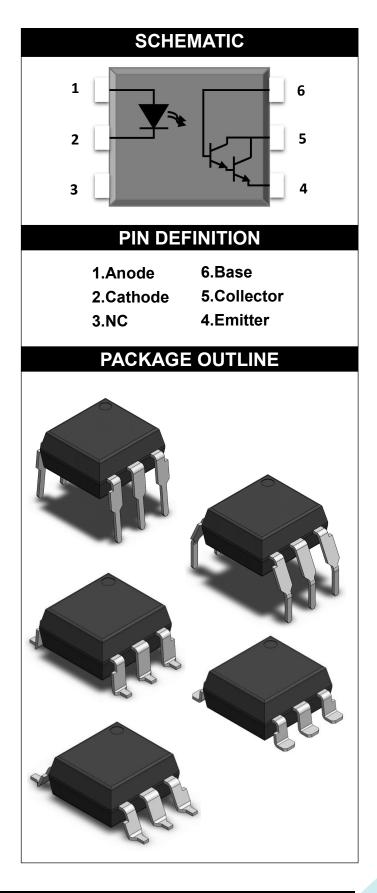
The 4N29, 4N30, 4N31, 4N32, 4N33 H11B1, H11B2, H11B3, H11B255 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic DIP6 package with different lead forming options

Features

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- Regulatory Approvals
 - UL UL1577
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - cUL- CSA Component Acceptance
 Service Notice No. 5A

Applications

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Interfacing coupling systems of different potentials and impedances





ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	VALUE	UNIT	NOTE			
INI	PUT						
Forward Current	I _F	60	mA				
Peak Forward Current(t=10µs)	I _{FM}	1	Α	1			
Reverse Voltage	V _R	6	V				
Power Dissipation(TA=25°C)	P _D	120	mW				
OUTPUT							
Collector - Emitter Voltage	V _{CEO}	55	V				
Collector-Base Breakdown Voltage	V _{CBO}	55	V				
Emitter - Collector Voltage	V _{ECO}	7	V				
Emitter-Base Breakdown Voltage	V _{EBO}	7	V				
Collector Current	Ic	150	mA				
Power Dissipation(TA=25°C)	Pc	150	mW				
COMMON							
Total Power Dissipation	Ptot	200	mW				
Isolation Voltage	Viso	5000	Vrms	2			
Operating Temperature	Topr	-55~+110	°C				
Storage Temperature	Tstg	-55~+110	°C				
Soldering Temperature	Tsol	260	°C				

Note 1. AC For 1 Minute, R.H. = $40 \sim 60\%$

Note 2. For 10 seconds

4N29, 4N30, 4N31, 4N32, 4N33, H11B1,H11B2,H11B3,H11B255

DIP6, DC Input, Photo Transistor Coupler

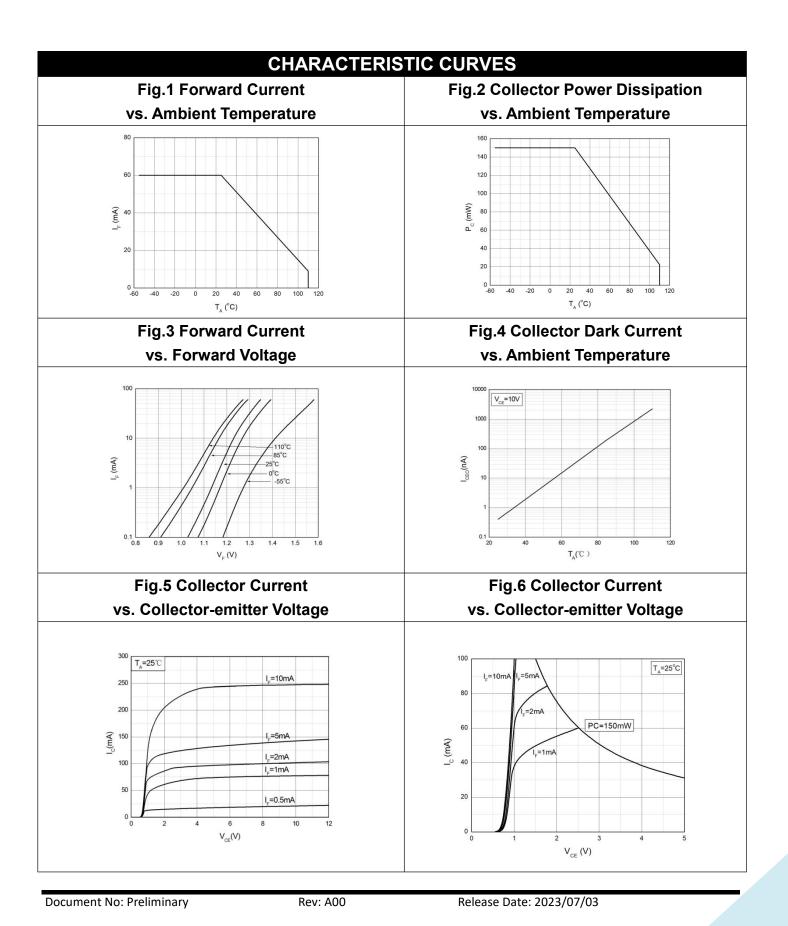
ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C								
PARAMETER	SYMBOL		MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE
	INPUT							
Forward Voltage	VF	/	-	1.24	1.4	V	IF=10mA	
		H11B3	-	1.4	1.5	V	IF=50mA	
Reverse Current	I	R	-	_	10	μA	VR=6V	
Input Capacitance	Cin		-	50	-	pF	V=0, f=1kHz	
OUTPUT								
Collector Dark Current	lc	EO	-	_	100	nA	VCE=10V	
Collector-Emitter Breakdown Voltage	BV	CEO	55	-	-	V	IC=0.1mA	
Collector-Base Breakdown Voltage	BV _{CBO}		55	-	-	V	IC=0.1mA	
Emitter-Collector Breakdown Voltage	BV _{ECO}		7	-	-	V	IE=0.1mA	

4N29, 4N30, 4N31, 4N32, 4N33, H11B1,H11B2,H11B3,H11B255

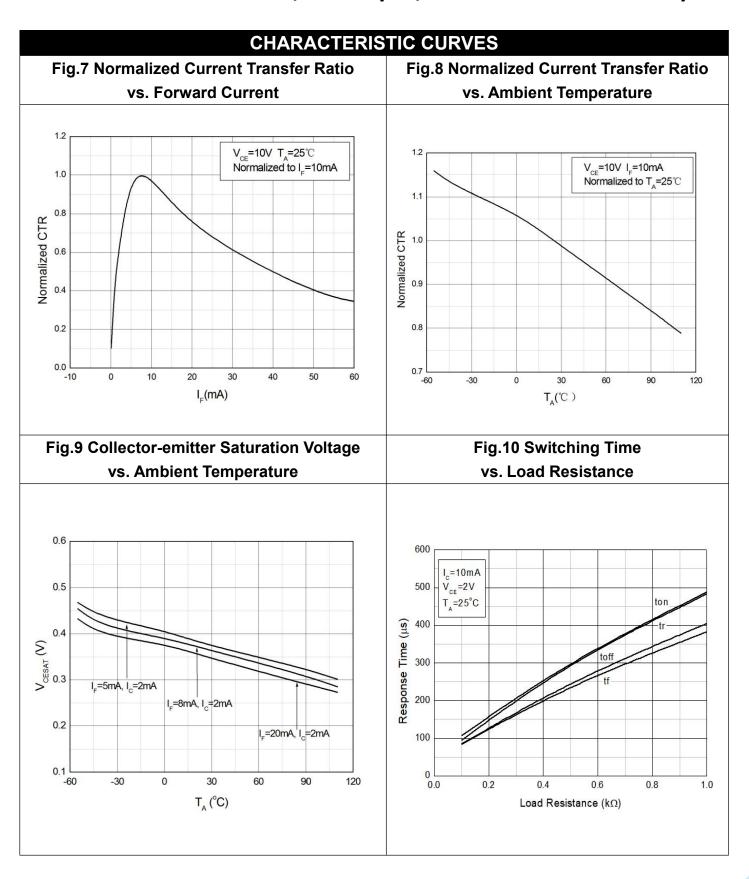
DIP6, DC Input, Photo Transistor Coupler

TRANSFER CHARACTERISTICS							
Current Transfer	CTR	4N31	50	-	-	%	
		4N29,4N30	100	-	-		IF=10mA, VCE=10V
		4N32,4N33	500	-	-		
		H11B1	500	-	-		
Ratio		H11B2	200	-	-		IF=1mA, VCE=5V
		H11B3	100	-	-		
		H11B255	100	-	-		IF=10mA, VCE=5V
Collector-Emitt er Saturation Voltage	V _{CE} (sat)	4N29,4N30, 4N32,4N33	-	-	1.0	V	IF= 8mA, IC= 2mA
		4N31	-	-	1.2		IF= 8mA, IC= 2mA
		H11B1,H11B2 H11B3	ı	-	1.0		IF= 1mA, IC= 1mA
		H11B255	-	-	1.0		IF= 50mA, IC= 50mA
Isolation Resistance	R _{IO}		10^11	-	-	Ω	Vio=500Vdc.
Floating Capacitance	C _{IO}		ı	8.0	-	pF	V=0, f=1MHz
Turn On Time	t _{on}	H11B1,H11B2 H11B3, H11B255	ı	25	-	μs	IC= 10mA, VCC= 2V, RL= 100Ω
		4N29,4N30, 4N31,4N32 4N33	1	-	5	μs	IC= 10mA, VCC= 2V, RL= 100Ω
Turn Off Time	e t _{off}	H11B1,H11B2 H11B3, H11B255	-	18	-	μs	IC= 10mA, VCC= 2V, RL= 100Ω
		4N32,4N33	-	-	100	μs	IC= 10mA, VCC= 2V,
		4N29,4N30, 4N31	-	-	40	μs	RL= 100Ω

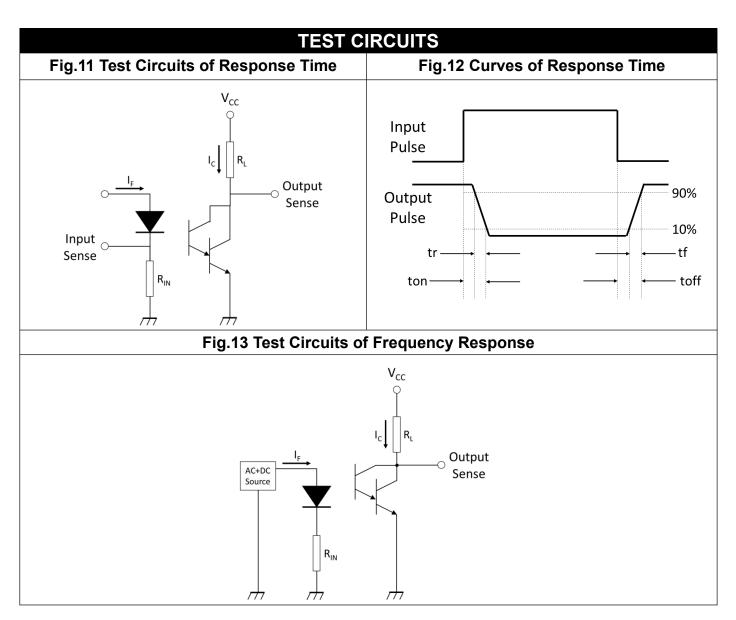






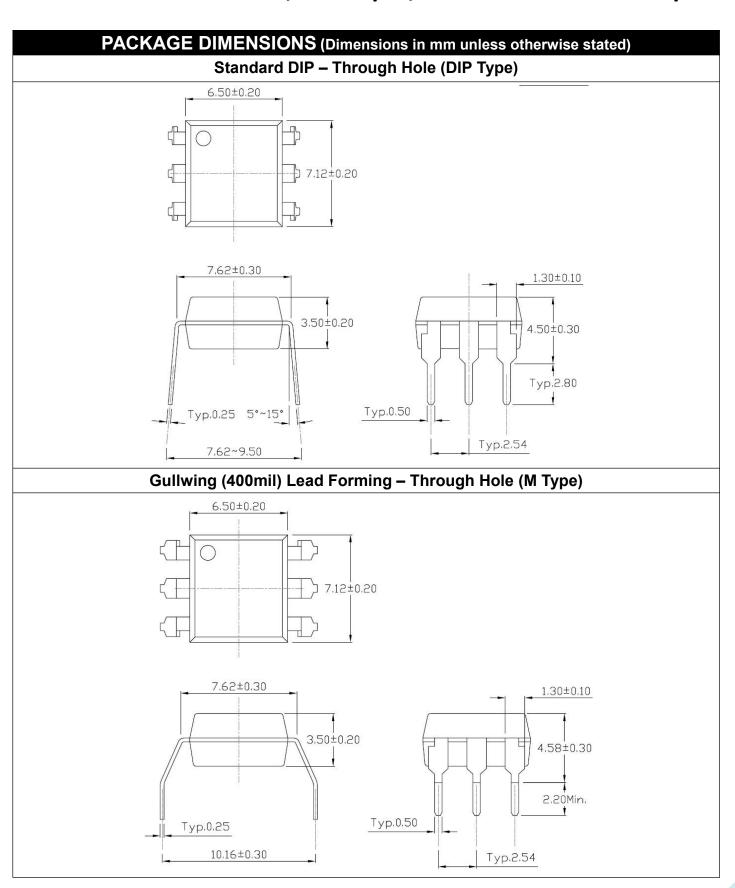








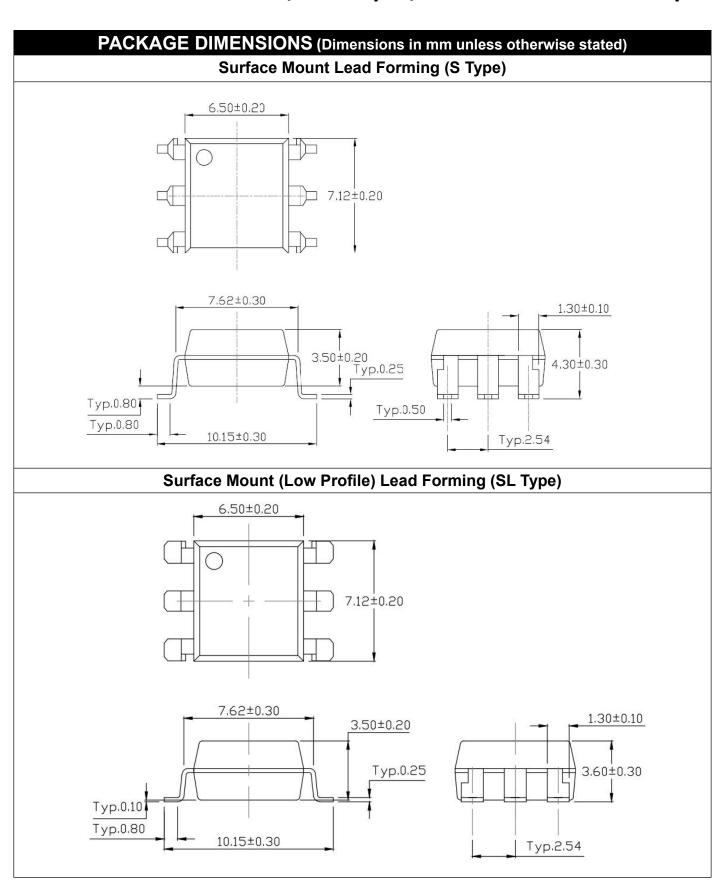
DIP6, DC Input, Photo Transistor Coupler



Rev: A00



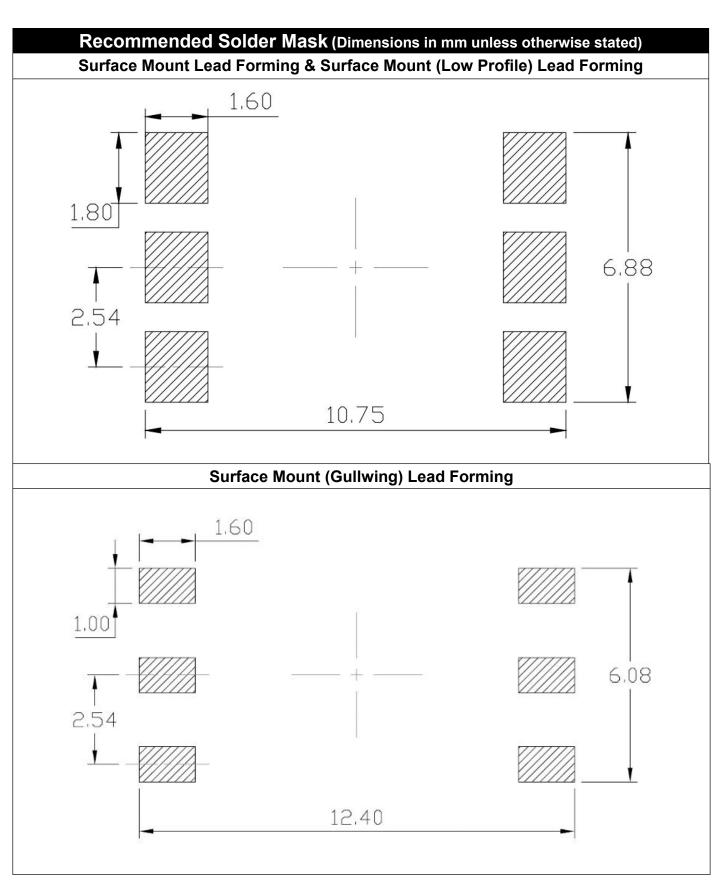
DIP6, DC Input, Photo Transistor Coupler



Rev: A00



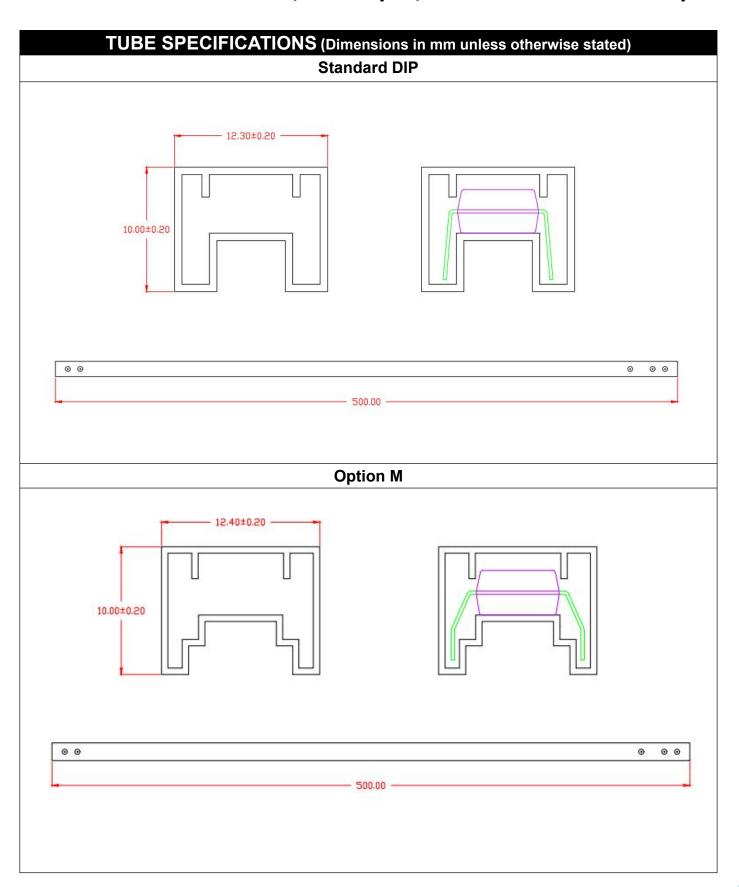
DIP6, DC Input, Photo Transistor Coupler



Rev: A00

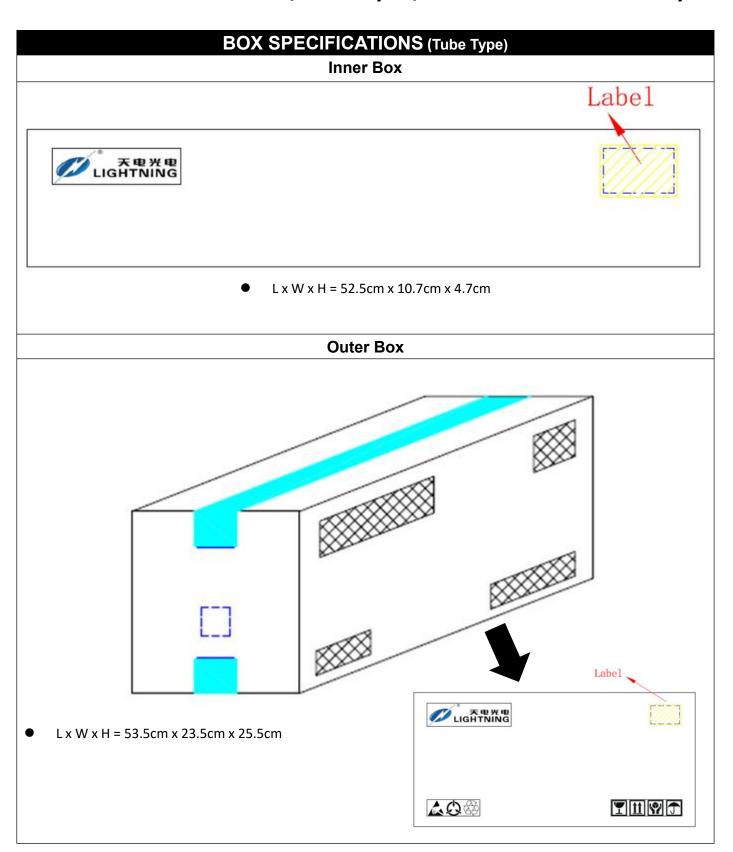


DIP6, DC Input, Photo Transistor Coupler



Rev: A00



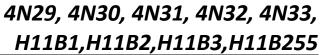


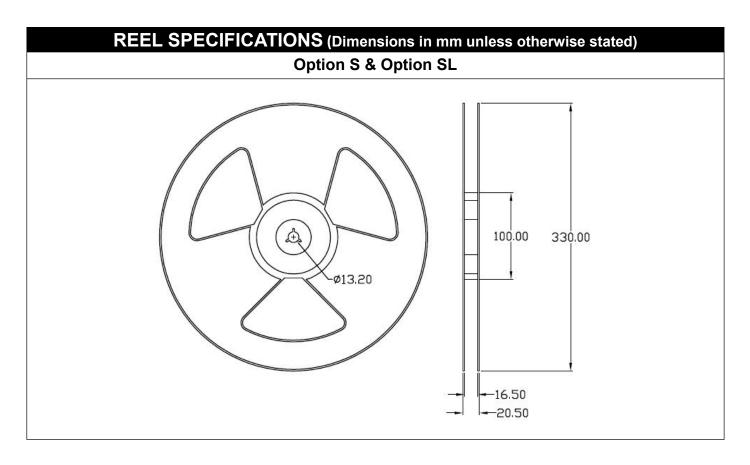


R

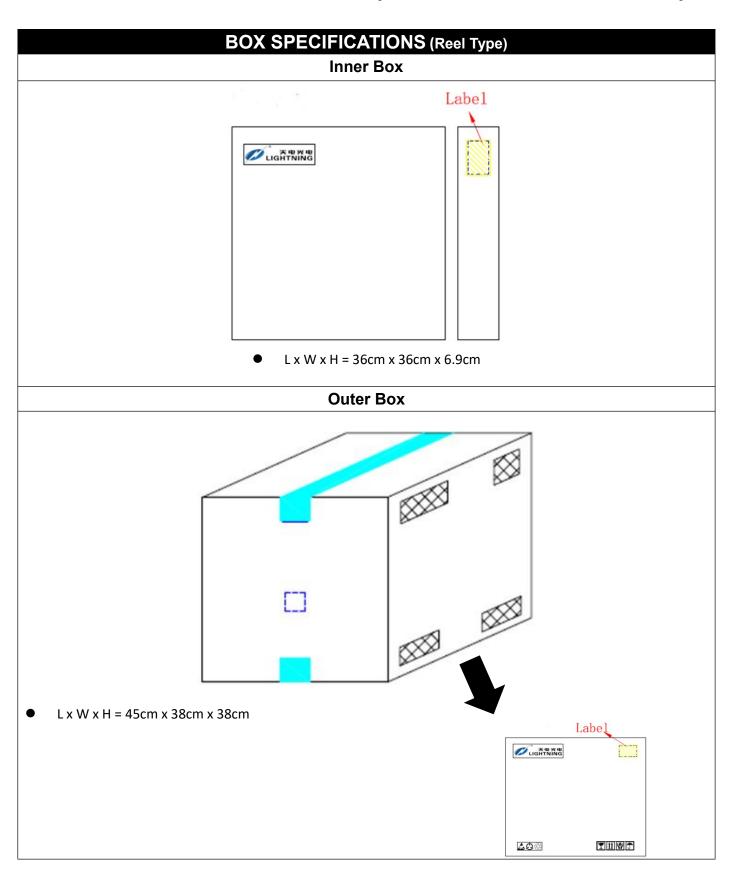
DIP6, DC Input, Photo Transistor Coupler

Carrier Tape Specifications (Dimensions in mm unless otherwise stated) Option S(T1) & SL(T1) 4,00 --- 2.00 Ø1.50 -1.757.50 16,00 -4.80-12.00Option S(T2) & SL(T2) 4.00 --2.00 Ø1.50 -1.757.50 16.00 4.80 -12.00









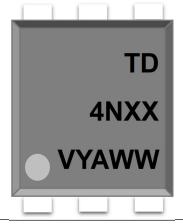




ORDERING AND MARKING INFORMATION

MARKING INFORMATION

4NXX



TD : Company Abbr.

: Part Number & Rank

V : VDE Option Y : Fiscal Year

A : Manufacturing Code

WW : Work Week

ORDERING INFORMATION

LABEL INFORMATION

4NXX(Y)(Z)-GV H11BX(Y)(Z)-GV

TD - Company Abbr.

4NXX/ – Part Number and Rank

(XX=29/30/31/32/33)

H11BX/ - Part Number and Rank

(X=1/2/3/255)

Y – Lead Form Option (M/S/SL/SLM/None)

Z – Tape and Reel Option (T1/T2)

G - Material Option

(G: Green, None: Non-Green)

V – VDE Option (V or None)



PACKING QUANTITY

Option	Quantity	Quantity – Inner box	Quantity – Outer box				
None	50 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 16k Units				
М	50 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box = 16k Units				
S(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units				
S(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units				
SL(T1)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units				
SL(T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box = 15k Units				

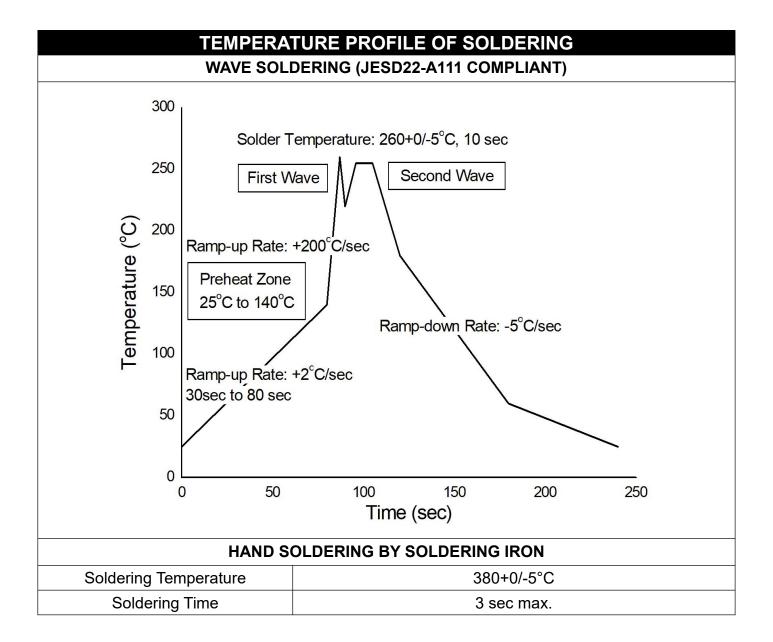


LIGHTNING

DIP6, DC Input, Photo Transistor Coupler

REFLOW INFORMATION REFLOW PROFILE Supplier T_p ≥ T_c User T_p ≤ T_c T_C -5°C Supplier t_p Tp Temperature 📑 T_c -5°C Max. Ramp Up Rate = 3°C/s Max. Ramp Down Rate = 6°C/s T_{L} T_{smax} Preheat Area T_{smin} 25 Time 25°C to Peak -Time ⇒ IPC-020d-5-1

Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	100	150°C
Temperature Max. (Tsmax)	150	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds	60-120 seconds
Ramp-up Rate (tL to tP)	3°C/second max.	3°C/second max.
Liquidous Temperature (TL)	183°C	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds	60 – 150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time (tP) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max	6°C/second max
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.



- One time soldering is recommended for all soldering method.
- Do not solder more than three times for IR reflow soldering.

4N29, 4N30, 4N31, 4N32, 4N33, H11B1,H11B2,H11B3,H11B255

DIP6, DC Input, Photo Transistor Coupler

DISCLAIMER

- LIGHTNING is continually improving the quality, reliability, function and design. LIGHTNING reserves the right to make changes without further notices.
- The characteristic curves shown in this datasheet are representing typical performance which are not guaranteed.
- LIGHTNING makes no warranty, representation or guarantee regarding the suitability of the products
 for any particular purpose or the continuing production of any product. To the maximum extent
 permitted by applicable law, LIGHTNING disclaims (a) any and all liability arising out of the
 application or use of any product, (b) any and all liability, including without limitation special,
 consequential or incidental damages, and (c) any and all implied warranties, including warranties of
 fitness for particular
- The products shown in this publication are designed for the general use in electronic applications such as office automation, equipment, communications devices, audio/visual equipment, electrical application and instrumentation purpose, non-infringement and merchantability.
- This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or lifesaving applications or any other application which can result in human injury or death.
- Please contact LIGHTNING sales agent for special application request.
- Immerge unit's body in solder paste is not recommended.
- Parameters provided in datasheets may vary in different applications and performance may vary
 over time. All operating parameters, including typical parameters, must be validated in each
 customer application by the customer's technical experts. Product specifications do not expand or
 otherwise modify LIGHTNING's terms and conditions of purchase, including but not limited to the
 warranty expressed therein.
- Discoloration might be occurred on the package surface after soldering, reflow or long-time use. It neither impacts the performance nor reliability.